MOSFETs Silicon P-Channel MOS (U-MOSVI)

# **TPCF8108**

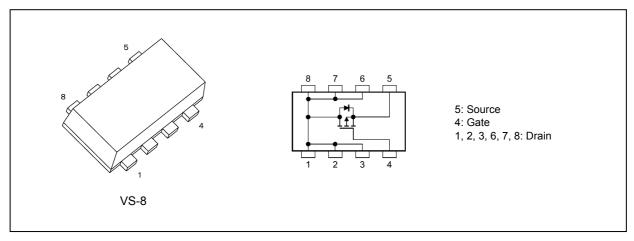
#### 1. Applications

- Lithium-Ion Secondary Batteries
- Power Management Switches
- Notebook PCs

#### 2. Features

- (1) Small footprint due to a small and thin package
- (2) Low drain-source on-resistance:  $R_{DS(ON)} = 21 \text{ m}\Omega$  (typ.) ( $V_{GS} = -4.5 \text{ V}$ )
- (3) Low leakage current:  $I_{DSS} = -10 \ \mu A \ (max) \ (V_{DS} = -20 \ V)$
- (4) Enhancement mode:  $V_{th}$  = -0.5 to -1.2 V (V\_{DS} = -10 V,  $I_{D}$  = -0.5 mA)

#### 3. Packaging and Internal Circuit



### 4. Absolute Maximum Ratings (Note) ( $T_a = 25^{\circ}C$ unless otherwise specified)

Characteris	Symbol	Rating	Unit		
Drain-source voltage			V <sub>DSS</sub>	-20	V
Gate-source voltage			V <sub>GSS</sub>	±12	
Drain current (DC)		(Note 1)	Ι <sub>D</sub>	-7	A
Drain current (pulsed)		(Note 1)	I <sub>DP</sub>	-28	
Power dissipation	(t = 5 s)	(Note 2)	PD	2.5	W
Power dissipation	(t = 5 s)	(Note 3)	PD	0.7	W
Single-pulse avalanche energy		(Note 4)	E <sub>AS</sub>	31.8	mJ
Avalanche current			I <sub>AR</sub>	-7	A
Channel temperature			T <sub>ch</sub>	150	°C
Storage temperature			T <sub>stg</sub>	-55 to 150	

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

#### 5. Thermal Characteristics

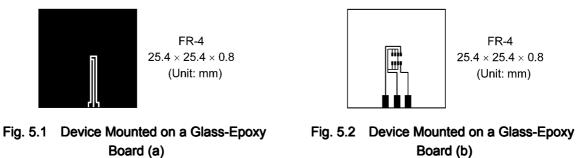
Characteristics				Max	Unit
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 2)	R <sub>th(ch-a)</sub>	50.0	°C/W
Channel-to-ambient thermal resistance	(t = 5 s)	(Note 3)	R <sub>th(ch-a)</sub>	178.5	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

Note 2: Device mounted on a glass-epoxy board (a), Figure 5.1

Note 3: Device mounted on a glass-epoxy board (b), Figure 5.2

Note 4: V\_DD = -16 V, T\_ch = 25°C (initial), L = 0.5 mH, R\_G = 25  $\Omega$ , I\_AR = -7 A



Note: This transistor is sensitive to electrostatic discharge and should be handled with care.

#### 6. Electrical Characteristics ( $T_a = 25^{\circ}C$ unless otherwise specified)

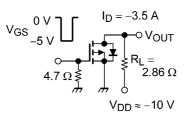
#### 6.1. Static Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage current	I <sub>GSS</sub>	$V_{GS}$ = ±12 V, $V_{DS}$ = 0 V	_	_	±0.1	μA
Drain cut-off current	I <sub>DSS</sub>	V <sub>DS</sub> = -20 V, V <sub>GS</sub> = 0 V	_	_	-10	
Drain-source breakdown voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 0 V	-20	_	—	V
Drain-source breakdown voltage (Note 5)	V <sub>(BR)DSX</sub>	I <sub>D</sub> = -10 mA, V <sub>GS</sub> = 8 V	-12	_	_	
Gate threshold voltage	V <sub>th</sub>	V <sub>DS</sub> = -10 V, I <sub>D</sub> = -0.5 mA	-0.5		-1.2	
Drain-source on-resistance	R <sub>DS(ON)</sub>	V <sub>GS</sub> = -1.8 V, I <sub>D</sub> = -1 A		45	95	mΩ
		V <sub>GS</sub> = -2.5 V, I <sub>D</sub> = -3.5 A		29	37	
		V <sub>GS</sub> = -4.5 V, I <sub>D</sub> = -3.5 A	_	21	26	

Note 5: If a forward bias is applied between gate and source, this device enters V<sub>(BR)DSX</sub> mode. Note that the drainsource breakdown voltage is lowered in this mode.

#### 6.2. Dynamic Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Input capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10 V, V <sub>GS</sub> = 0 V, f = 1 MHz	_	1320	_	pF
Reverse transfer capacitance	C <sub>rss</sub>		—	180	—	
Output capacitance	C <sub>oss</sub>		_	210	_	
Switching time (rise time)	t <sub>r</sub>	See Figure 6.2.1.	_	8.6	_	ns
Switching time (turn-on time)	t <sub>on</sub>		_	17	—	
Switching time (fall time)	t <sub>f</sub>			42	—	
Switching time (turn-off time)	t <sub>off</sub>			152	_	



Duty  $\leq$  1%,  $t_W = 10~\mu s$ 

#### Fig. 6.2.1 Switching Time Test Circuit

#### 6.3. Gate Charge Characteristics

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Total gate charge (gate-source plus gate-drain)	Qg	$V_{DD} \approx$ -16 V, $V_{GS}$ = -5 V, $I_D$ = -7 A	_	19	—	nC
Gate-source charge 1	Q <sub>gs1</sub>			2.5		
Gate-drain charge	Q <sub>gd</sub>		_	5.2		

#### 6.4. Source-Drain Characteristics

Characteristics		Symbol	Test Condition	Min	Тур.	Max	Unit
Pulsed reverse drain current (1	Note 6)	I <sub>DRP</sub>	—		_	-28	А
Diode forward voltage		V <sub>DSF</sub>	I <sub>DR</sub> = -7 A, V <sub>GS</sub> = 0 V	-	_	1.2	V

Note 6: Ensure that the channel temperature does not exceed 150°C.

### 7. Marking

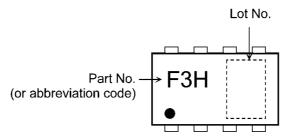
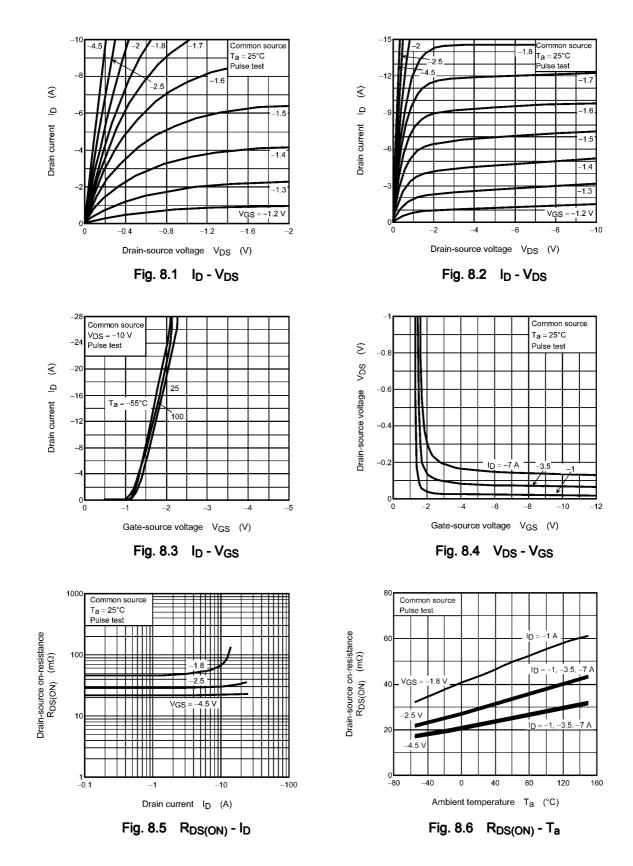
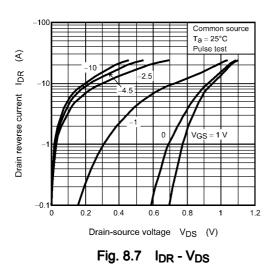


Fig. 7.1 Marking

### 8. Characteristics Curves (Note)





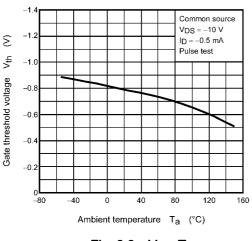
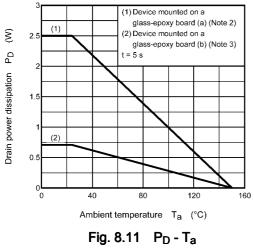


Fig. 8.9 V<sub>th</sub> - T<sub>a</sub>



(Guaranteed Maximum)

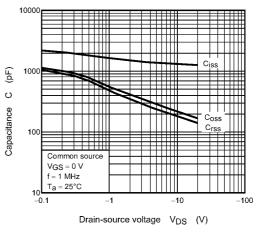


Fig. 8.8 Capacitance - VDS

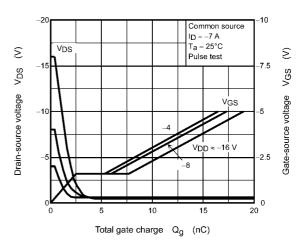


Fig. 8.10 Dynamic Input/Output Characteristics

(2

(1

Single pulse

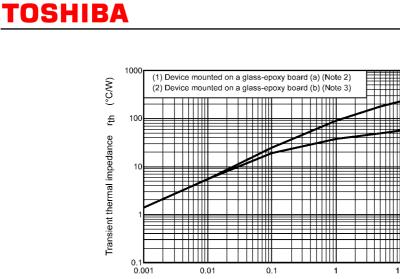
1111

1000

10

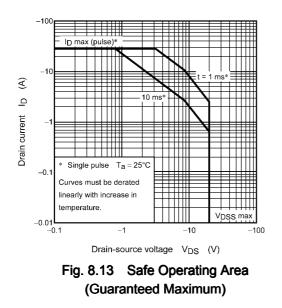
11111

100



Pulse width tw (s) Fig. 8.12 rth - tw

(Guaranteed Maximum)

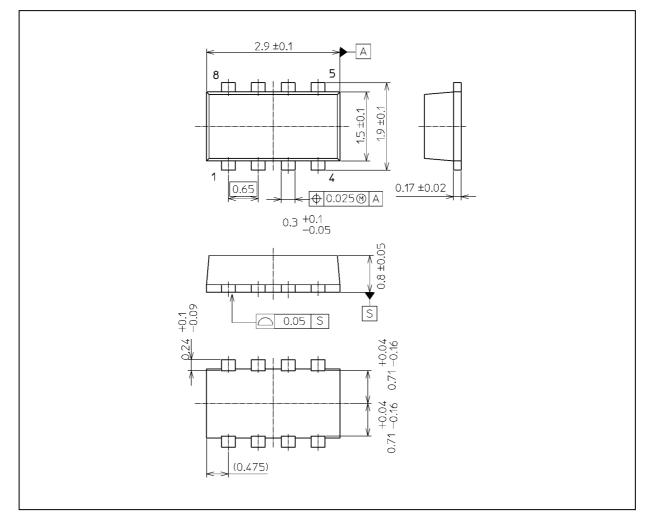


Note: The above characteristics curves are presented for reference only and not guaranteed by production test, unless otherwise noted.

### **TPCF8108**

#### **Package Dimensions**

Unit: mm



#### Weight: 0.011 g (typ.)

	Package Name(s)
TOSHIBA: 2-3U1S	
Nickname: VS-8	

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